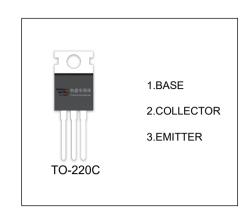


# **2SB857** TRANSISTOR (PNP)

#### **FEATURES**

Low Frequency Power Amplifier



## MAXIMUM RATINGS ( $T_a$ =25 $^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-70	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	P <sub>C</sub> Collector Power Dissipation		Α
Pc			W
$R_{\theta JA}$			°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

## **ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25**°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10μA,I <sub>E</sub> =0	-70			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> =-50mA,I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA,I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V,I <sub>E</sub> =0			-1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V,I <sub>C</sub> =0			-1	μA
DC current gain	h <sub>FE(1)</sub> *	V <sub>CE</sub> =-4V, I <sub>C</sub> =-1A	60		320	
De current gam	h <sub>FE(2)</sub> *	V <sub>CE</sub> =-4V, I <sub>C</sub> =-0.1A	35			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =-2A,I <sub>B</sub> =-200mA			-1	V
Base-emitter voltage	V <sub>BE</sub> *	V <sub>CE</sub> =-4V, I <sub>C</sub> =-1A			-1	V
Transition frequency	f <sub>T</sub> *	V <sub>CE</sub> =-4V,I <sub>C</sub> =-500mA		15		MHz

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

#### **CLASSIFICATION OF h**<sub>FE(1)</sub>

RANK	В	С	D					
RANGE	60-120	100-200	160-320					